

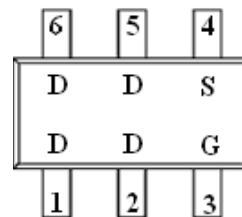
### ➤ General Description

This PAN4440H N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent  $R_{ds(On)}$  performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

### ➤ Feature

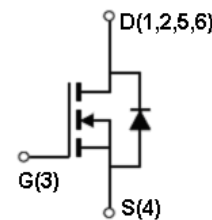
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Battery Voltage Operation
- SOT-363 package design

### ➤ SOT-363



### ➤ Application

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Load/Power Switching Smart Phones, Pagers
- PA Switch
- Level Switch



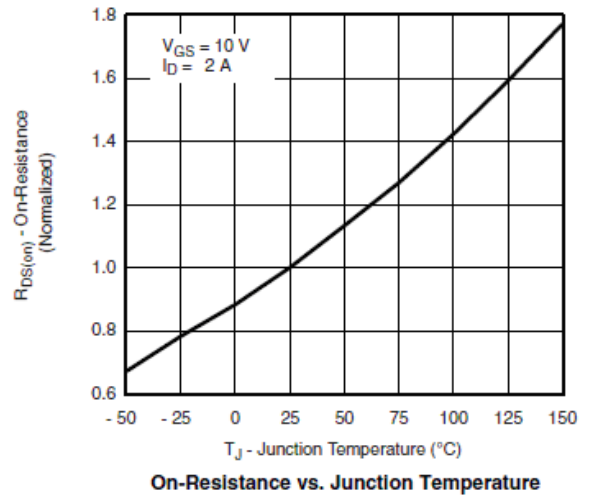
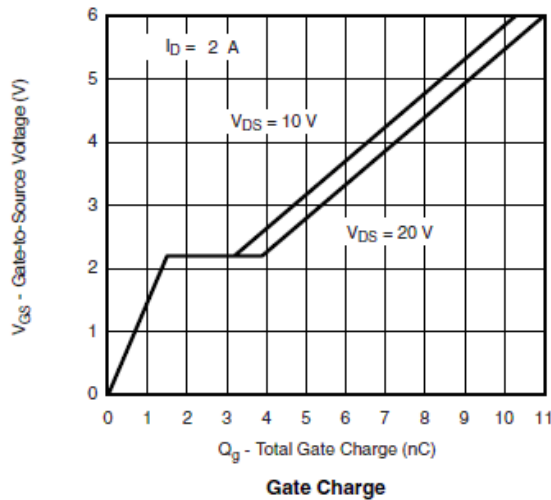
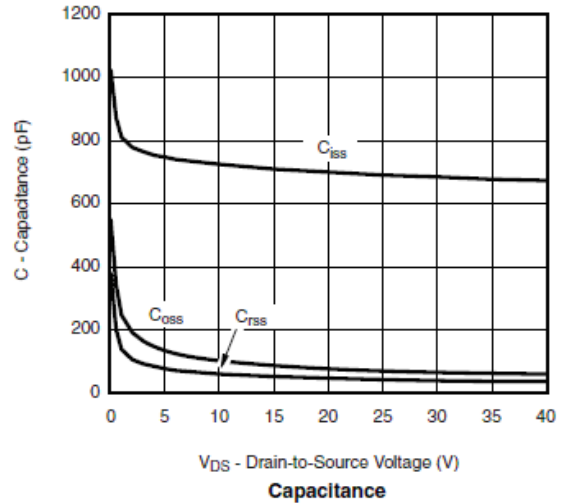
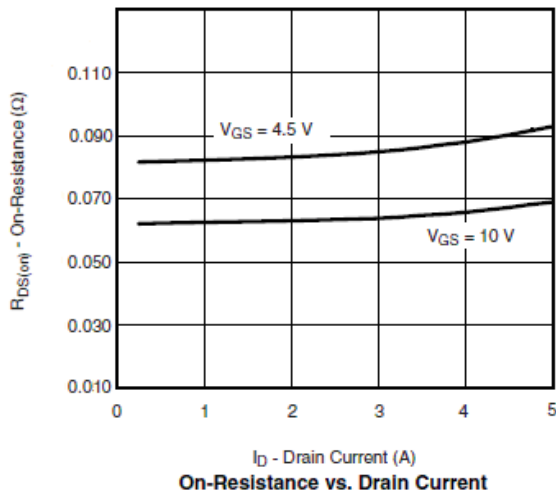
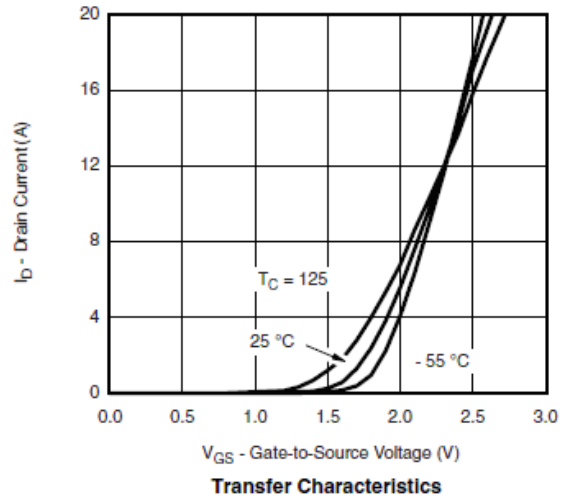
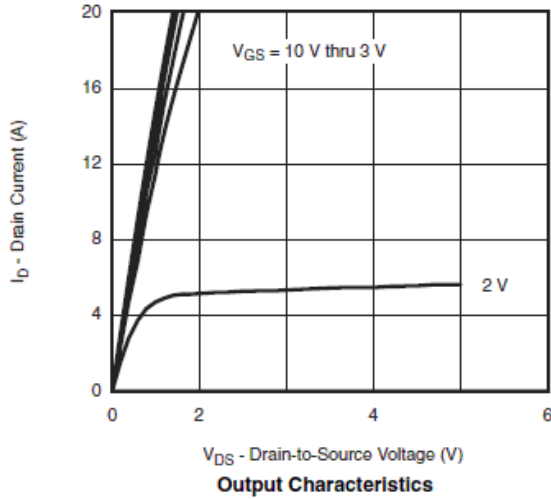
### ➤ Absolute Maximum Ratings

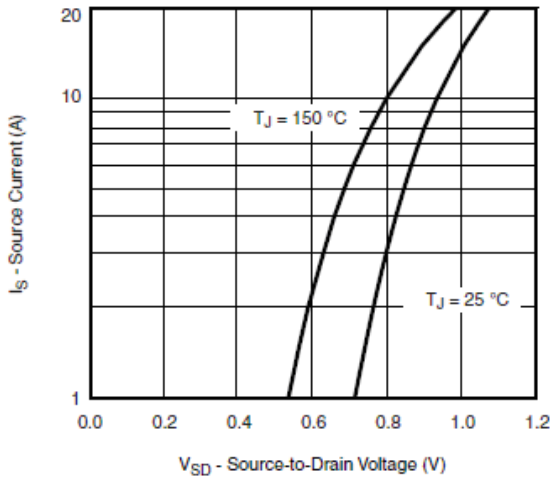
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DSS}$	40	V
Gate -Source Voltage	$V_{GSS}$	$\pm 20$	V
Continuous Drain Current( $T_J=150^\circ C$ )	$I_D$	$T_A=25^\circ C$	3.6
		$T_A=70^\circ C$	2.8
Pulsed Drain Current	$I_{DM}$	7	A
Continuous Source Current(Diode Conduction)	$I_S$	1.3	A
Power Dissipation	$P_D$	$T_A=25^\circ C$	1.5
		$T_A=70^\circ C$	1.0
Operating Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature Range	$T_{STG}$	-55/150	$^\circ C$
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	120	$^\circ C/W$

➤ **Electrical Characteristics ( $T_A=25^\circ C$  Unless otherwise noted)**

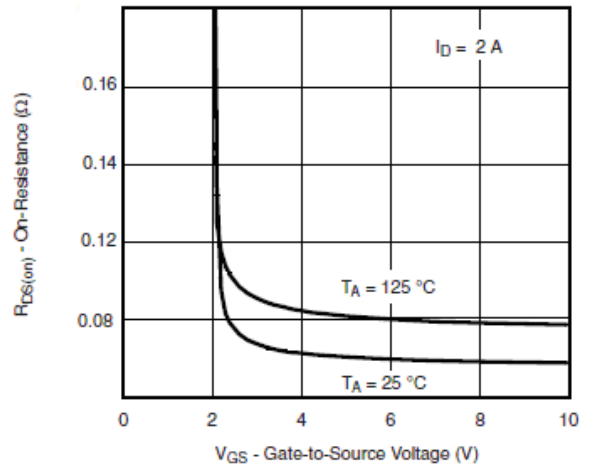
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	40			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0		2.0	
Gate Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 20V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=40V, V_{GS}=0V$			1	uA
		$V_{DS}=40V, V_{GS}=0V$ $T_J=85^\circ C$			10	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \geq 5V, V_{GS}=10V$	10			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=3.6A$		40	50	m $\Omega$
		$V_{GS}=4.5V, I_D=2.8A$		50	65	
Forward Transconductance	$g_{FS}$	$V_{DS}=10V, I_D=2.0A$		16		S
Diode Forward Voltage	$V_{SD}$	$I_S=1.5A, V_{GS}=0V$		0.85	1.2	V
<b>Dynamic</b>						
Total Gate Charge	$Q_g$	$V_{DS}=20V, V_{GS}=4.5V$ $I_D=2A$		10	15	nC
Gate-Source Charge	$Q_{gs}$			2		
Gate-Drain Charge	$Q_{gd}$			2.5		
Input Capacitance	$C_{iss}$	$V_{DS}=20V, V_{GS}=0V$ $f=1MHz$		650		pF
Output Capacitance	$C_{oss}$			75		
Reverse Transfer Capacitance	$C_{rss}$			45		
Turn-On Time	$t_{d(on)}$	$V_{DD}=15V, R_L=15\Omega$ $I_D=1A, V_{GEN}=10V$ $R_G=6\Omega$		8	15	ns
	$t_r$			12	20	
Turn-Off Time	$t_{d(off)}$			28	40	
	$t_f$			8	15	

### ➤ Typical Characteristics

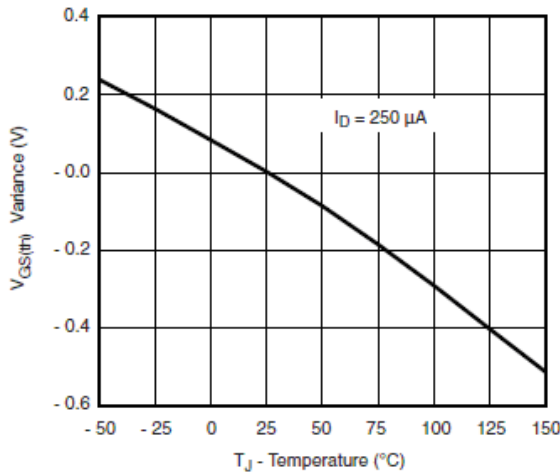




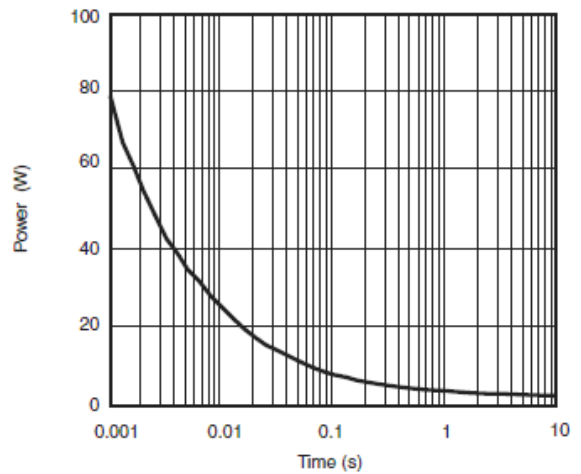
Source-Drain Diode Forward Voltage



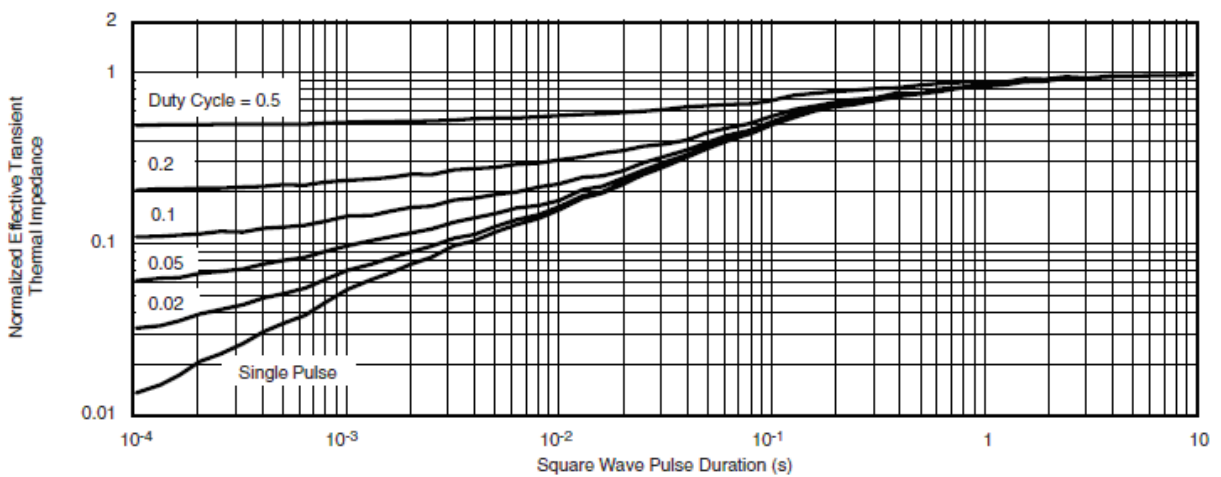
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

➤ Recommend IR Reflow Soldering Thermal Profile

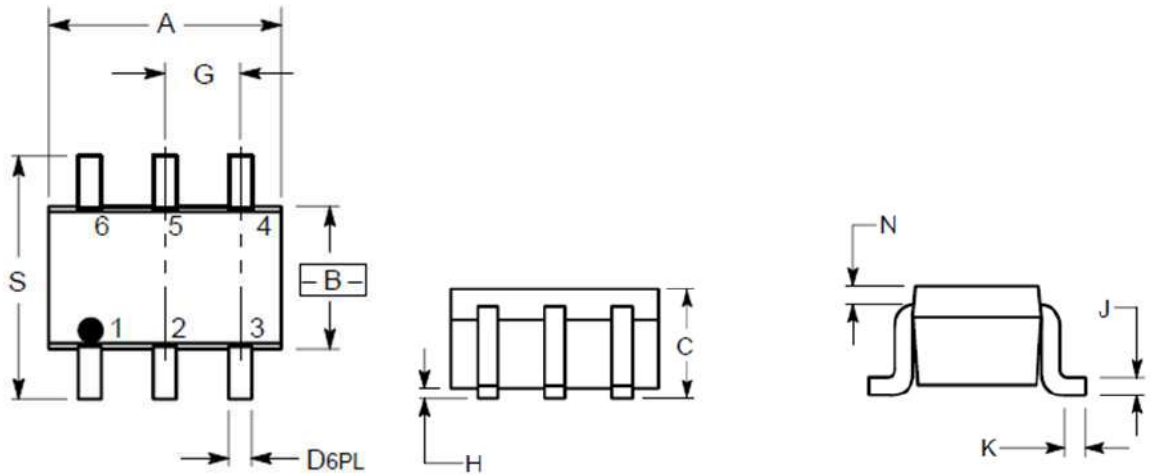


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T <sub>smin</sub> )	150°C
Temperature Max. (T <sub>smax</sub> )	200°C
Time (t <sub>s</sub> ) from (T <sub>smin</sub> to T <sub>smax</sub> )	60-120 seconds
Average Ramp-up Rate (t <sub>L</sub> to t <sub>P</sub> )	3°C/second max.
Liquidous Temperature (T <sub>L</sub> )	217°C
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (t <sub>P</sub> ) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➤ Ordering Information

Part Number	Description	Quantity
PAN4440H	SOT-363 Reel	3000 pcs

➤ Package Information ( SOT-363 )



$\oplus 0.2 (0.008) \text{ (M)}$   $B \text{ (M)}$

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

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